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**HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS****Features:**

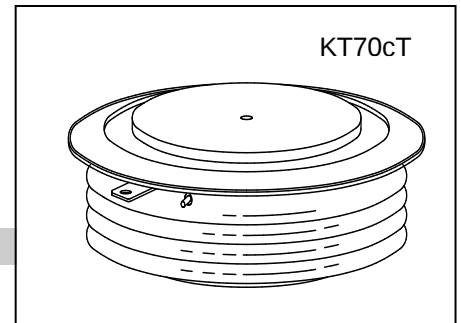
- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 4200 volts
- . High dv/dt Capability
- . Pressure Assembled Device

**ELECTRICAL CHARACTERISTICS AND RATINGS****Blocking - Off State**

| Device Type | V <sub>RRM</sub> (1) | V <sub>DRM</sub> (1) | V <sub>RSM</sub> (1) |
|-------------|----------------------|----------------------|----------------------|
| KP1900/36   | 3600                 | 3600                 | 3700                 |
| KP1900/38   | 3800                 | 3800                 | 3900                 |
| KP1900/40   | 4000                 | 4000                 | 4100                 |
| KP1900/42   | 4200                 | 4200                 | 4300                 |

V<sub>RRM</sub> = Repetitive peak reverse voltageV<sub>DRM</sub> = Repetitive peak off state voltageV<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

|                                                       |                                    |                    |
|-------------------------------------------------------|------------------------------------|--------------------|
| Repetitive peak reverse leakage and off state leakage | I <sub>RRM</sub> /I <sub>DRM</sub> | 5 mA<br>120 mA (3) |
| Critical rate of voltage rise                         | dv/dt (4)                          | 1000 V/μsec        |



Notes:

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +125 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T<sub>j</sub> = 125 °C.
- (4) Minimum value for linear and exponential waveshape to 67% rated V<sub>DRM</sub>. Gate open. T<sub>j</sub> = 125 °C.
- (5) The value of di/dt is established in accordance with EIA/NIMA Standard JB/T 8950.2-2013

**Conducting - On State**

| Parameter                                     | Symbol             | Min. | Max.                | Typ. | Units            | Conditions                                                                        |
|-----------------------------------------------|--------------------|------|---------------------|------|------------------|-----------------------------------------------------------------------------------|
| Average value of on-state current             | I <sub>T(AV)</sub> |      | 1900                |      | A                | Sinewave, 180° conduction, T <sub>c</sub> = 70°C                                  |
| RMS value of on-state current                 | I <sub>TRMS</sub>  |      | 2983                |      | A                | Nominal value                                                                     |
| Peak one cycle surge (non repetitive) current | I <sub>TSM</sub>   |      | 22800               |      | A                | 10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, T <sub>j</sub> = 125 °C |
| I square t                                    | I <sup>2</sup> t   |      | 2.6x10 <sup>6</sup> |      | A <sup>2</sup> s | 10 msec                                                                           |
| Latching current                              | I <sub>L</sub>     |      | 1000                |      | mA               | V <sub>D</sub> = 12 V; R <sub>L</sub> = 12 ohms                                   |
| Holding current                               | I <sub>H</sub>     |      | 200                 |      | mA               | V <sub>D</sub> = 12 V; I = 2.5 A                                                  |
| Peak on-state voltage                         | V <sub>TM</sub>    |      | 2.3                 |      | V                | I <sub>TM</sub> = 3000A; T <sub>j</sub> = 25°C                                    |
| Threshold voltage, low-level                  | V <sub>TO</sub>    |      | 1.14                |      | V                | T <sub>j</sub> = 125°C                                                            |
| Slope resistance, low-level                   | r <sub>T</sub>     |      | 0.25                |      | mΩ               | 1000A to 3000A                                                                    |
| Critical rate of rise of on-state current     | di/dt              |      | 200                 |      | A/μs             | Repetition                                                                        |

### Gating

| Parameter                      | Symbol      | Min. | Max. | Typ. | Units | Conditions                                                                  |
|--------------------------------|-------------|------|------|------|-------|-----------------------------------------------------------------------------|
| Peak gate power dissipation    | $P_{GM}$    |      | 20   |      | W     |                                                                             |
| Average gate power dissipation | $P_{G(AV)}$ |      | 4    |      | W     |                                                                             |
| Gate-trigger current           | $I_{GT}$    |      | 200  |      | mA    | $V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^{\circ}\text{C}$ |
| Gate- trigger voltage          | $V_{GT}$    | 0.70 | 2.5  |      | V     | $V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^{\circ}\text{C}$ |
| Peak negative voltage          | $V_{GRM}$   |      | 5    |      | V     |                                                                             |

### Dynamic

| Parameter                                 | Symbol   | Min. | Max. | Typ. | Units         | Conditions                                                                                                                                                              |
|-------------------------------------------|----------|------|------|------|---------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Delay time                                | $t_d$    |      | 3.0  | 2.5  | $\mu\text{s}$ | $I_{TM} = 100\text{ A}; V_D = 67\% V_{DRM}$<br>Gate pulse: $V_G = 30\text{ V}; R_G = 10\text{ ohms};$<br>$t_r = 0.1\mu\text{s}; t_p = 20\mu\text{s}$                    |
| Turn-off time (with $V_R = -5\text{ V}$ ) | $t_q$    |      |      | 600  | $\mu\text{s}$ | $I_{TM} = 1000\text{ A}; di/dt = -10\text{ A}/\mu\text{s};$<br>$V_R = 50\text{ V}; dV/dt = 30\text{ V}/\mu\text{s};$<br>$V_D = 67\% V_{DRM}; T_j = 125^{\circ}\text{C}$ |
| Reverse recovery charge                   | $Q_{rr}$ |      |      | 2500 | $\mu\text{C}$ | $I_{TM} = 1000\text{ A}; di/dt = -10\text{ A}/\text{s};$<br>$V_R = 50\text{ V}; T_j = 125^{\circ}\text{C}$                                                              |

### THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

| Parameter                             | Symbol            | Min. | Max.   | Typ. | Units                       | Conditions          |
|---------------------------------------|-------------------|------|--------|------|-----------------------------|---------------------|
| Operating temperature                 | $T_j$             | -40  | +125   |      | $^{\circ}\text{C}$          |                     |
| Storage temperature                   | $T_{stg}$         | -40  | +140   |      | $^{\circ}\text{C}$          |                     |
| Thermal resistance - junction to case | $R_{\theta(j-c)}$ |      | 0.0125 |      | $^{\circ}\text{C}/\text{W}$ | Double sided cooled |
| Thermal resistance - case to heatsink | $R_{\theta(c-s)}$ |      | 0.004  |      | $^{\circ}\text{C}/\text{W}$ | Double sided cooled |
| Mounting force                        | P                 |      |        | 33   | kN                          |                     |
| Weight                                | W                 |      |        | 0.85 | kg                          |                     |

\* Mounting surfaces smooth, flat and greased

